

<b>Notice of References Cited</b>			Application/Control No. 09/700,236	Applicant(s)/Patent Under Reexamination ZHANG ET AL.	
Examiner Matthew J Song			Art Unit 1765	Page 1 of 1	

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5,679,152	10-1997	Tischler et al.	117/97
	B	US-5,290,393	03-1994	Nakamura, Shuji	438/509
	C	US-5,980,631	11-1999	Tews et al.	117/89
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	DE 19652548 C1	03-1998	Germany	TEWS et al.	H01L 21/20
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Tischler et al. "Defect Reduction in GaAs epitaxial layers using GaAsP-InGaAs strained layer superlattice", Appl. Phys. Lett., 4 (3), 1 February 1985, pp 294-296.
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.